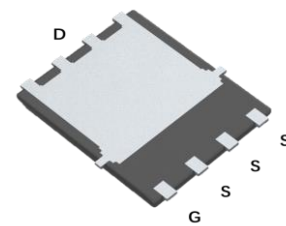
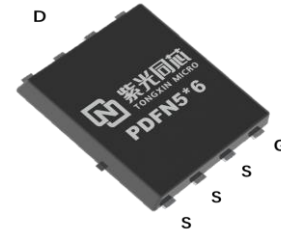


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Product Summary

Parameter	Value	Unit
V_{DS}	150	V
$V_{GS(th)}_{Typ}$	3	V
I_D (@ $V_{GS} = 10V$) ⁽¹⁾	86	A
$R_{DS(ON)}_{Typ}$ (@ $V_{GS} = 10V$)	9.5	m Ω

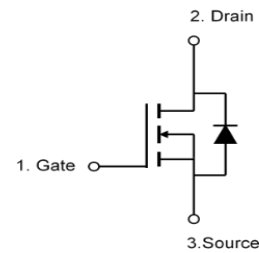


Features

- Fast Switching
- Very low on-resistance
- Enhancement mode
- 100% Avalanche Tested
- 100% ΔV_{ds} Tested
- Halogen-free and RoHS-compliant

Typical Applications

- Load Switch
- PWM Application
- Power Management



Product Validation

- Qualified for Industrial Applications According to The Relevant Tests of JEDEC47/20/22

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Ordering Information

Device	Package	Quantity of Pins	Marking	MSL	T _J (°C)
THF010S150HKN1	PDFN5x6-8L	8	010S150HKN	1	-55 to 150

Absolute Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DS}	150	V
Gate-to-Source Voltage	V _{GS}	±20	V
Continuous Drain Current ⁽¹⁾	I _D	T _C = 25°C	86
		T _C = 100°C	54
Pulsed Drain Current ⁽²⁾	I _{DM}	344	A
Avalanche Current ⁽³⁾	I _{AS}	38	A
Avalanche Energy ⁽³⁾	E _{AS}	217	mJ
Power Dissipation ⁽⁴⁾	P _D	T _C = 25°C	139
		T _C = 100°C	56
Junction & Storage Temperature Range	T _J , T _{STG}	-55 to 150	°C

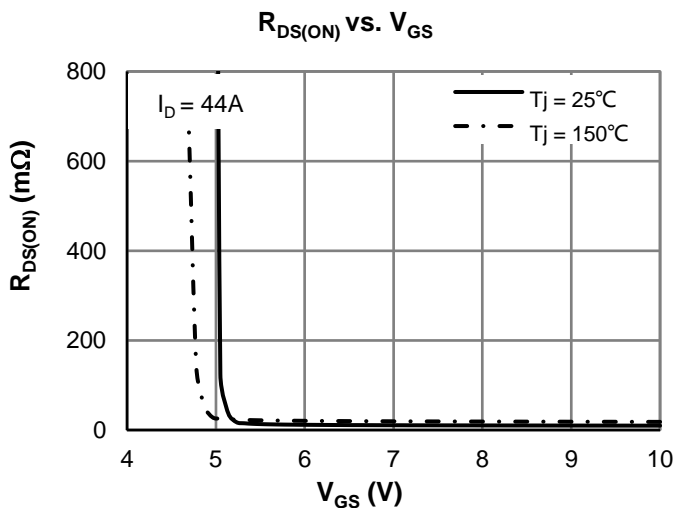


Figure 1: R_{DS(ON)} VS. V_{GS}

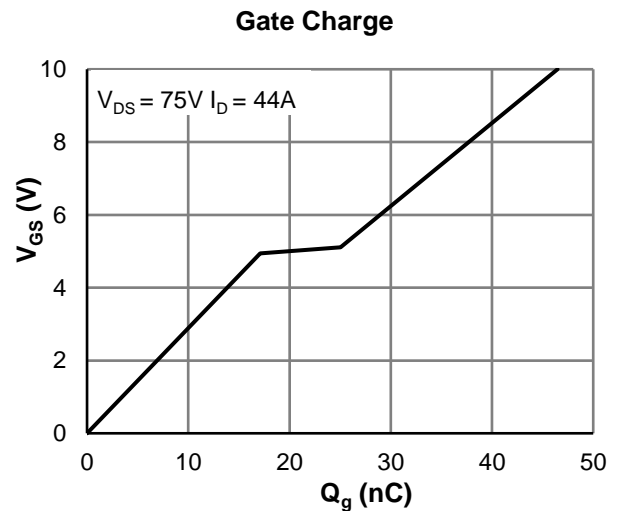


Figure 2: Gate Charge Curve

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Electrical Characteristics (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	150	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 150\text{V}$, $V_{GS} = 0\text{V}$	-	-	1.0	μA
Gate-Body Leakage Current	I_{GSS}	$V_{DS} = 0\text{V}$, $V_{GS} = \pm 20\text{V}$	-	-	100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	2.2	3.0	3.8	V
Static Drain-Source ON-Resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{V}$, $I_D = 44\text{A}$	-	9.5	10.0	m Ω
		$V_{GS} = 7\text{V}$, $I_D = 44\text{A}$	-	10.2	12.2	
Diode Forward Voltage	V_{SD}	$I_S = 44\text{A}$, $V_{GS} = 0\text{V}$	-	0.9	1.2	V
Diode Continuous Current	I_S	$T_C = 25^\circ\text{C}$	-	-	116	A
DYNAMIC PARAMETERS ⁽⁵⁾						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 75\text{V}$, $f = 1\text{MHz}$	-	3443	-	pF
Output Capacitance	C_{oss}		-	262	-	pF
Reverse Transfer Capacitance	C_{rss}		-	9	-	pF
Gate Resistance	R_g	$V_{GS} = 0\text{V}$, $V_{DS} = 0\text{V}$, $f = 1\text{MHz}$	-	0.8	-	Ω
SWITCHING PARAMETERS ⁽⁵⁾						
Total Gate Charge (@ $V_{GS} = 10\text{V}$)	Q_g	$V_{GS} = 0$ to 10V $V_{DS} = 75\text{V}$, $I_D = 44\text{A}$	-	47	-	nC
Gate Source Charge	Q_{gs}		-	17.1	-	nC
Gate Drain Charge	Q_{gd}		-	7.9	-	nC
Turn-On DelayTime	$t_{D(on)}$	$V_{GS} = 10\text{V}$, $V_{DS} = 75\text{V}$ $I_D = 44\text{A}$, $R_{GEN} = 3\Omega$	-	16.0	-	ns
Turn-On Rise Time	t_r		-	5	-	ns
Turn-Off DelayTime	$t_{D(off)}$		-	22	-	ns
Turn-Off Fall Time	t_f		-	6	-	ns
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 44\text{A}$, $dI_F/dt = 100\text{A}/\mu\text{s}$	-	72	-	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	280	-	nC

Thermal Performance

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	-	50	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	-	0.9	$^\circ\text{C}/\text{W}$

Notes:

1. Computed continuous current assumes the condition of T_{J_Max} while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. This single-pulse measurement was taken under T_{J_Max} .
3. This single-pulse measurement was taken under the following condition [$L = 0.3\text{mH}$, $V_{GS} = 10\text{V}$, $V_{DS} = 75\text{V}$] while its value is limited by T_{J_Max} .
4. The power dissipation P_D is based on T_{J_Max} .
5. This value is guaranteed by design hence it is not included in the production test.

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Typical Electrical & Thermal Characteristics

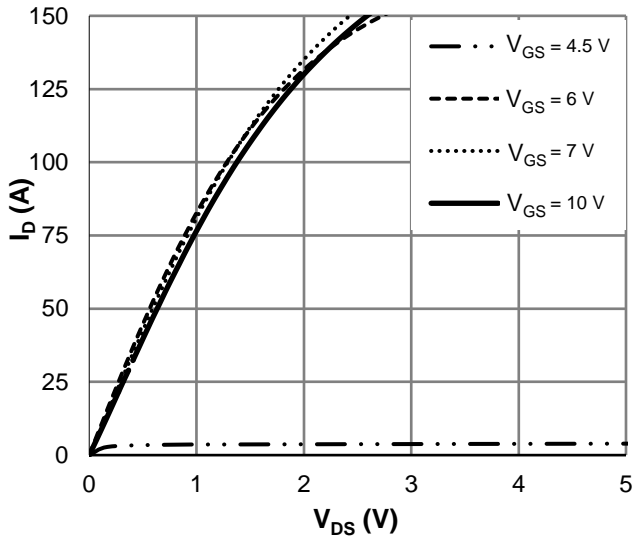


Figure 3: Saturation Characteristics

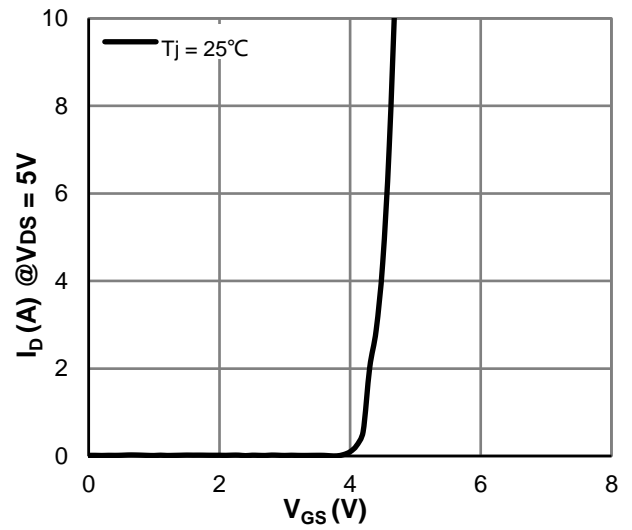


Figure 4: Transfer Characteristics

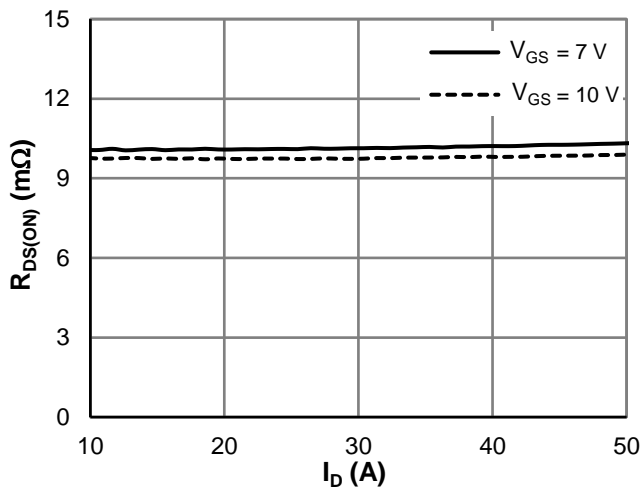


Figure 5: R_DS(ON) vs. Drain Current

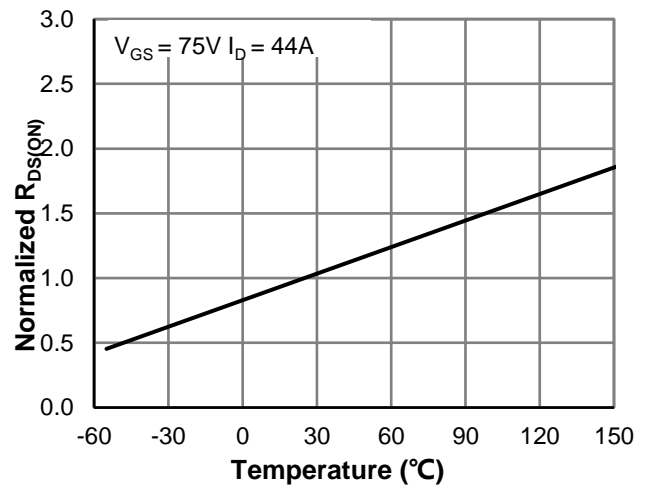


Figure 6: R_DS(ON) vs. Junction Temperature

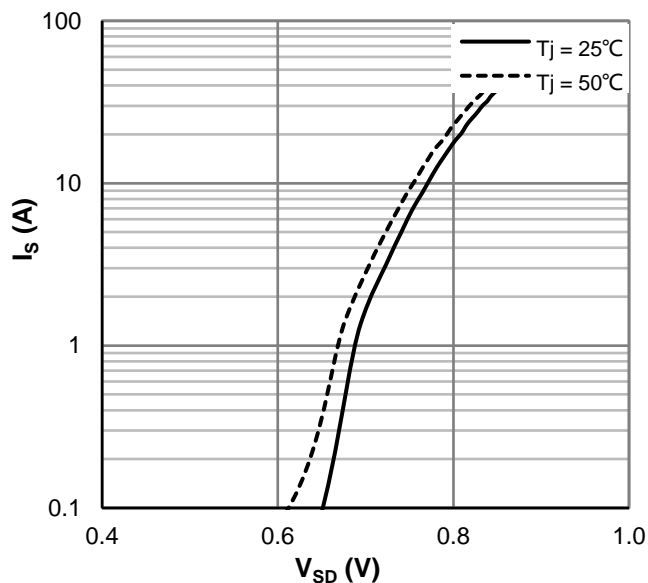


Figure 7: Body-Diode Characteristics

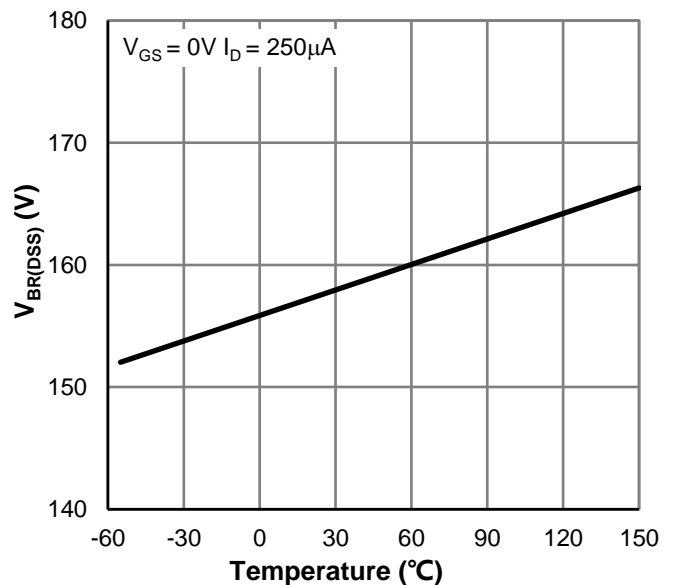


Figure 8: V_BR(DSS) vs. Junction Temperature

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Typical Electrical & Thermal Characteristics

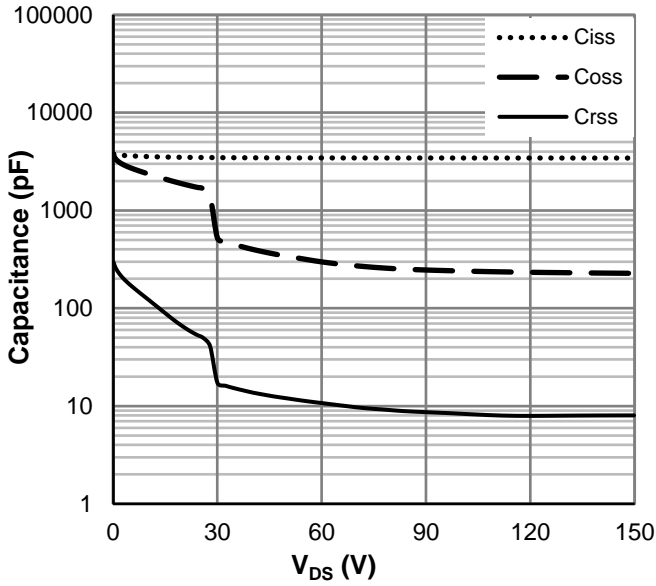


Figure 9: Capacitance Characteristics

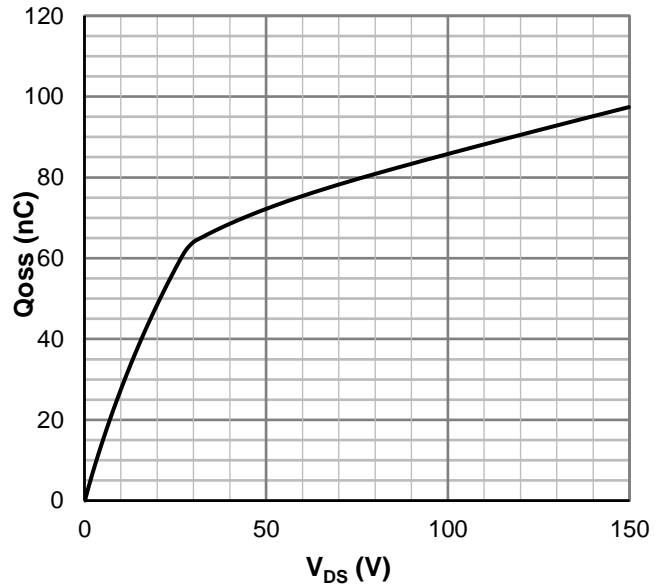


Figure 10: Coss Stored Energy

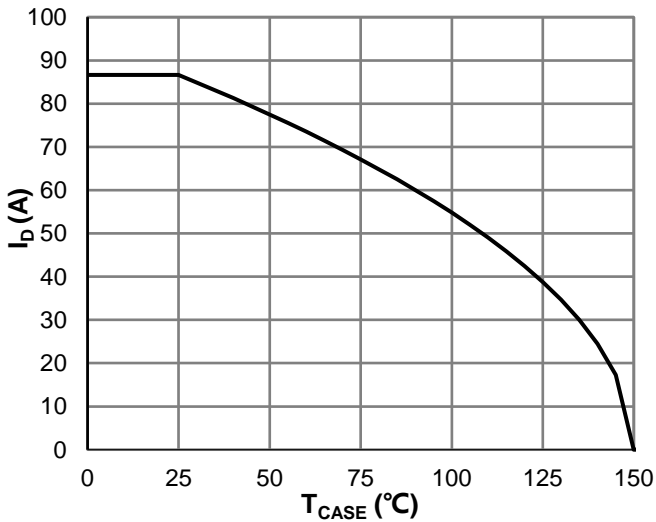


Figure 11: Current De-rating

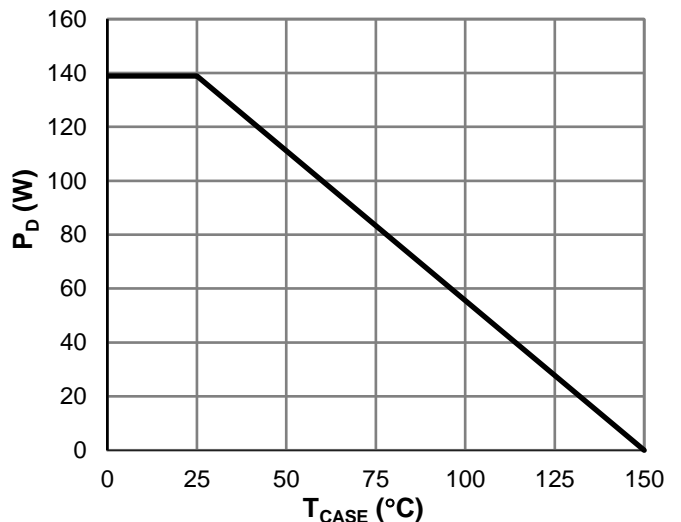


Figure 12: Power De-rating

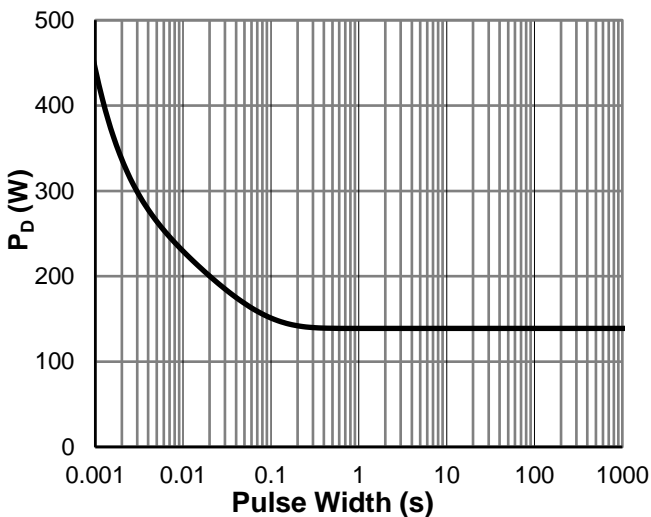


Figure 13: Single Pulse Power Rating, Junction-to-Case

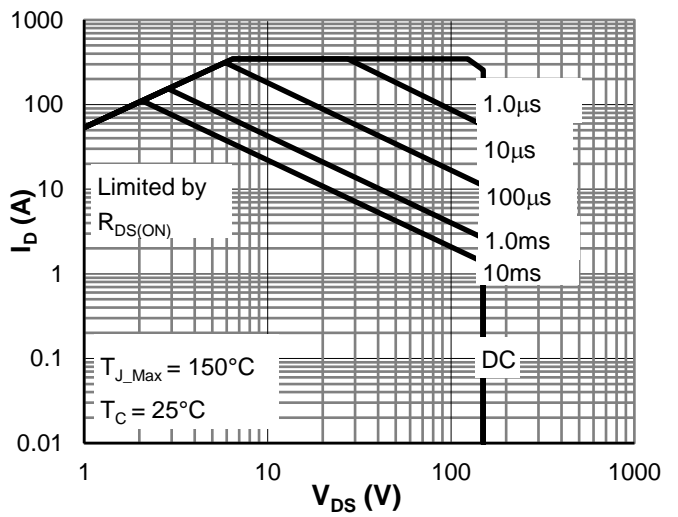


Figure 14: Maximum Safe Operating Area

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Typical Electrical & Thermal Characteristics

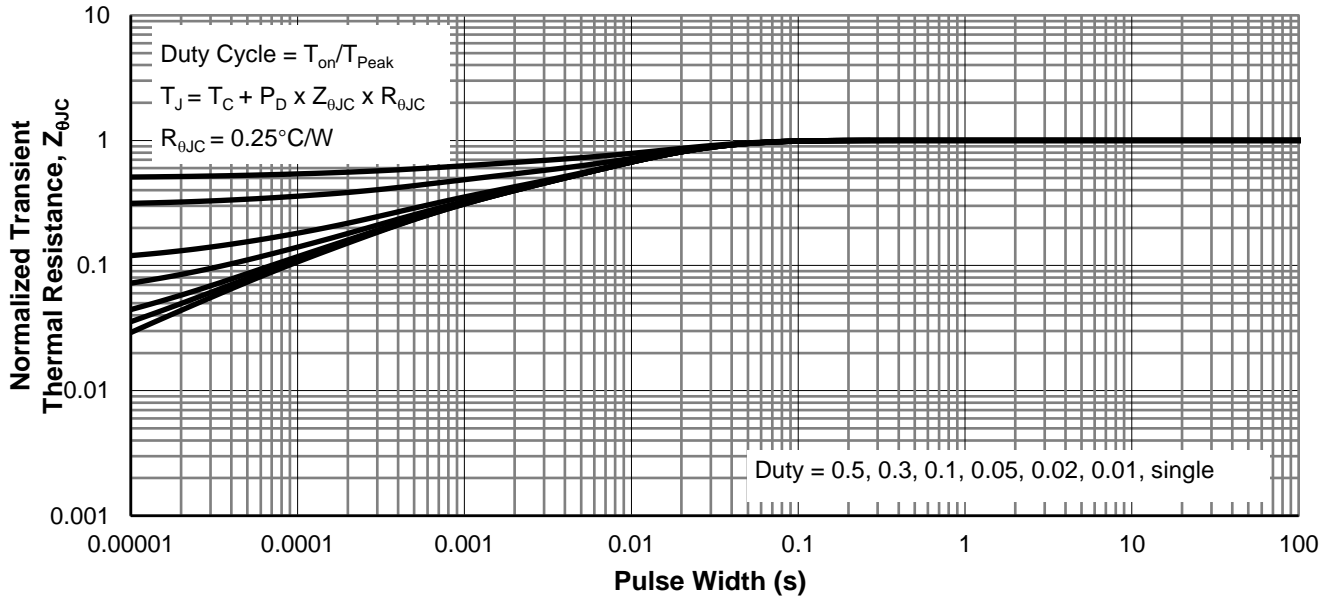


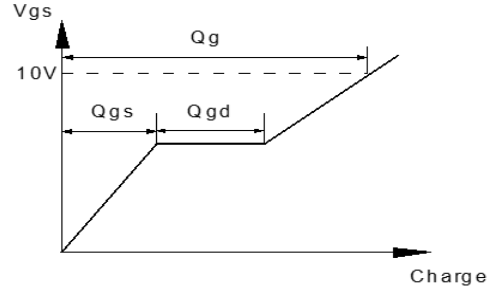
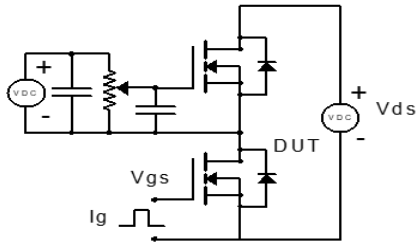
Figure 15: Normalized Maximum Transient Thermal Impedance

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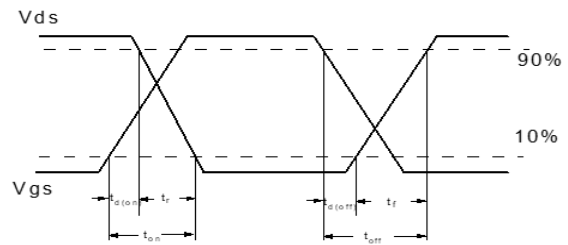
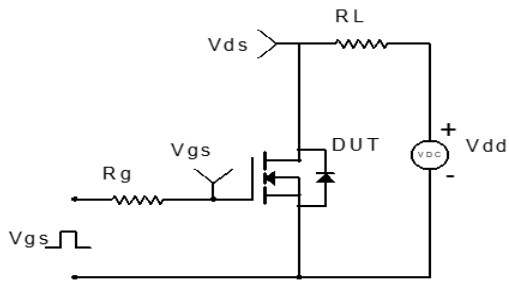
Datasheet

Test Condition

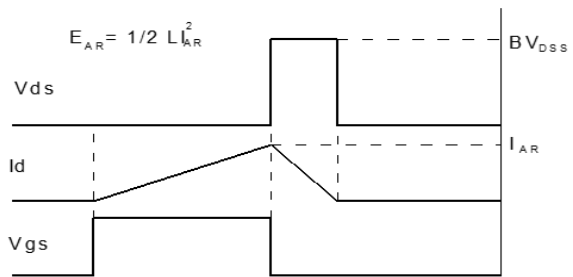
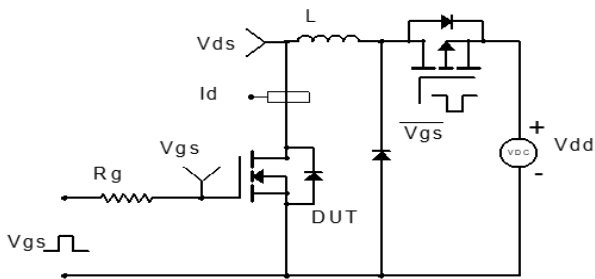
Gate Charge Test Circuit & Wave Form



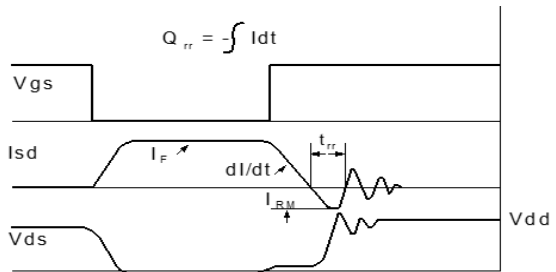
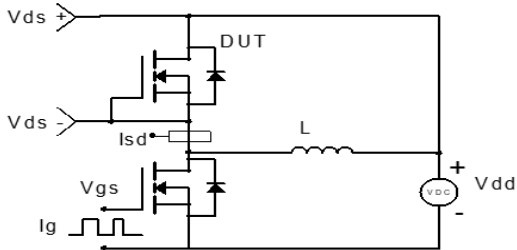
Resistive Switching Test Circuit & Wave Form



Unclamped Inductive Switching (UIS)



Diode Recovery Test Circuit & Wave Form

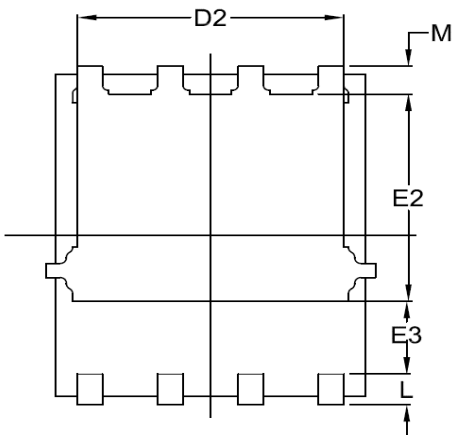
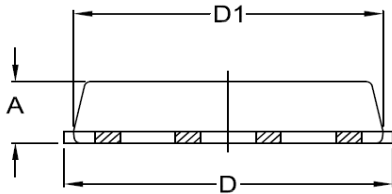
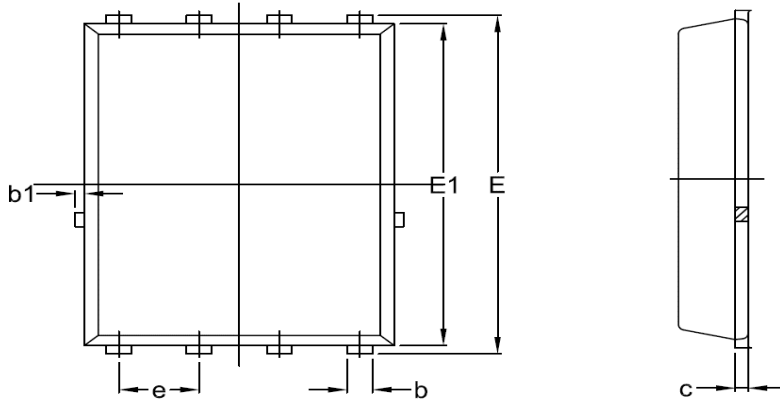


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Package Outlines

Package Drawing PDFN5*6



DIM	MILLIMETERS		
	MIN	NOM	MAX
A	1.00	1.10	1.20
b	0.30	0.40	0.50
b1	0.02	0.15	0.22
c	0.15	0.20	0.35
D	4.95	5.15	5.35
D1	4.80	4.90	5.00
D2	4.00	4.20	4.40
E	5.95	6.05	6.25
E1	5.65	5.75	5.85
E2	3.50	3.70	3.90
E3	1.10	/	/
e	1.27		
L	0.40	0.55	0.70
M	0.35	0.50	0.65

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Revision History

Version	Change Description
V1.0	initial version

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